Sunday, September 1 10:30-16:00 Short Course 1(Room A (407)), Short Course 2 (Room B+C (408+409)) Special Talk Session (Grand Hall Foyer) 18:00-19:30 Welcome Reception (Grand Hall Foyer) Monday, September 2 9:00-12:50 Opening and Plenary Sessions (Grand Hall) Room M (Special Conference Room D (Medium Hall) Room E (401) Room G (403) Room H (Small Hall) Room J (Main Studio) Room K (404) Room A (407) **Room B (408) Room C (409)** Room F (402) 14:30-16:00 14:30-15:45 14:30-15:45 14:30-16:00 14:30-15:45 14:30-15:30 14:30-15:30 14:15-15:45 14:30-15:45 [D-1] Ga2O3 Power Devices [A-1] Advanced CMOS: Process Technology [B-1] Ferroelectric Memory Materials [C-1] Advanced Metallization I [F-1] Thermoelectric materials and devices I [H-1] Device-I [K-1] Oxide-TFTs I [J-1] Qubit I [M-1] Oxide Materials 16:15-17:30 16:15-17:30 16:15-17:30 16:15-17:15 16:15-16:45 16:30-17:30 16:15-17:30 16:15-17:15 16:15-17:30 16:15-17:30 [A-2] Innovative devices and Sensing [B-2] In-Memory and Unconventional [E-2] Integrated Light Source and Related [C-2] MEMS and Advanced Metallization I [F-2] Thermoelectric materials and devices II [K-2] Oxide-TFTs II [D-2] Diamond Devices [H-2] Characterization-I [J-2] Qubit II [M-2] Characterization and Device Applications Technology technology Computing I **18:30-21:00** Banquet (Himeji Castle) Tuesday, September 3 Room M (Special Conference Room) Room D (Medium Hall) Room J (Main Studio) Room K (404) **Room B (408)** Room C (409) **Room E (401)** Room F (402) Room G (403) Room H (Small Hall) Room A (407) 9:00-10:15 9:00-10:00 9:00-10:15 9:00-10:00 9:00-10:00 9:00-10:00 [G-3] Organic / Molecular / Bio-electronics Late [B-3] Ferroelectric Devices [D-3] Si-related Devices [E-3] Si Photonics [H-3] Growth [J-3] Novel Quantum Devices News Session 10:45-12:15 10:45-12:00 10:45-12:00 10:45-11:45 10:45-12:15 10:45-11:45 10:45-12:00 10:45-12:00 10:45-12:00 10:45-12:00 [B-4] Ferroelectric Memory Devices [A-4] Advanced CMOS: Device Technology [C-4] Advanced integration [D-4] High-speed Devices [G-4] Highly Sensitive Devices for Chem/Bio [E-4] UV and Visible Light Technology [F-4] Energy harvesting and solar cells [H-4] Device-II [M-4] Wide Bandgap Materials [J-4] Spintronics 13:30-14:00 13:30-14:20 13:30-13:48 13:30-14:06 13:30-13:54 13:30-13:46 13:30-13:48 13:30-13:52 13:30-13:52 13:30-14:30 13:30-13:54 Short Oral Presentation 15:00-17:00 Poster Session (Exibition Hall A) Wednesday, September 4 Room M (Special Conference Room D (Medium Hall) Room H (Small Hall) Room A (407) Room B (408) Room C (409) Room E (401) Room F (402) Room G (403) Room J (Main Studio) Room K (404) 9:00-10:15 9:00-10:15 9:00-10:00 9:00-10:30 9:00-10:15 9:00-10:15 9:00-10:00 9:00-10:00 [J-5] Novel devices for neuromorphic [B-5] In-Memory and Unconventional [C-5] Advanced Metallization II [D-5] SiC MOS Interfaces [G-5] Advanced Devices for Medical Applications [H-5] Characterization-II [A-5] Ferroelectric Devices [M-5] Advanced Materials and Thin Films Computing II applications 10:45-12:15 10:45-12:15 10:45-12:15 10:45-12:00 11:00-12:00 10:30-12:00 10:45-11:45 10:45-11:15 10:30-12:00 10:45-12:00 [A-6] Modeling, Simulation and [G-6] Advanced Lab-on-Chip Devices and [C-6] MEMS and Advanced Metallization II [D-6] SiC Power Devices [B-6] 3D NAND Flash Memory [F-6] Solar cells [H-6] Device-III [K-6] Group-IV Thin-film Technologies [M-6] Low Dimensional Materials [J-6] Novel advanced materials

Characterization

13:30-14:45

[A-7] Advanced CMOS: CFET

13:30-14:45

[B-7] ReRAM, PCRAM, and FeRAM

15:15-16:30

[B-8] Ferroelectric FET

13:30-14:45

[D-7] GaN Power Devices

15:15-16:15

[D-8] Processes and Characterization

13:30-14:45

[E-7] Metamaterials and Metasurfaces

15:15-16:00

[E-8] Sensors and Detectors

Room N (Studio 1)

14:30-15:45

[N-1] Sensor Circuits and Systems

Room N (Studio 1)

10:45-12:15

[N-4] Emerging Memory Devices, and DRAM

13:30-13:38

Short Oral Presentation

Room N (Studio 1)

10:45-12:00

[N-6] Compute-in-Memory

13:30-14:45

[N-7] Advanced Circuits and Devices

Area Scope	Area 1: Advanced CMOS: Material Science / Process Engineering / Device Technology	oe	Area 7: Organic / Molecular / Bio-electronics
	Area 2: Advanced and Emerging Memories / New Applications		Area 8: Low Dimensional Devices and Materials
	Area 3: Heterogeneous and 3D Integration / Interconnect / MEMS		Area 9: Novel Functional / Quantum / Spintronic Devices and Materials
	Area 4: Power / High-speed Devices and Materials		Area 10: Thin Film Electronics: Oxide / Non-single Crystalline / Novel Process
	Area 5: Photonics: Devices / Integration / Related Technology		Area 11: Advanced Materials: Synthesis / Crystal Growth / Characterization
	Area 6: Energy Harvesting and Converting Devices and Materials		Area12: Advanced Circuits / Systems Interacting with Innovative Devices and Materials

Organic/Inorganic Hybrid Electronics

13:30-14:45

[G-7] Organic Electronics I

15:15-16:30

[G-8] Organic Electronics II

13:30-14:15

[H-7] Device-IV

13:30-14:45

[K-7] Ferroelectric Materials and Late News

13:30-15:15

[M-7] Group IV Materials